Laboratory 3: Configurable Amplifiers Using Small-Signal MOS Resistors

Preliminary Exercises

This lab focuses on the use of MOS transistors as voltage-controlled variable resistors. In the lab, we will specifically demonstrate a gain-controllable (i.e., configurable) inverting amplifier and a bandwidth-controllable lowpass filter using op amps, resistors, capacitors, and a discrete MOS transistor.

The preliminary exercises in this section aim to prepare you for this lab. In completing these exercises, you should assume an NMOS transistor with the following parameters:

Transconductance Parameter, $K_n=\mu_n C_{ox}(W/L)$:	1220 $\mu A/V^2$
Nominal Threshold Voltage, V_{to}:	1.37 V
Surface Potential, $2\phi_f$:	1.1 V
Body Effect Parameter, γ:	2.5 $V^{1/2}$

Other device parameters can be found in the 'cd4007ub.mod' file online, which is a SPICE model.

1. MOS transistor small-signal resistance

(a) For the MOS transistor circuit shown in Fig. PL3.1(a) below, calculate and tabulate (using the *Results Sheet for Preliminary Exercises*) the values of the small-signal resistance R_{MOS} from drain to source for values of control voltage V_C ranging from 0V to 10V, in steps of 1V. Then, plot your values of R_{MOS} versus V_C on a graph. Again, assume the MOS device parameters given at the beginning of this pre-lab.

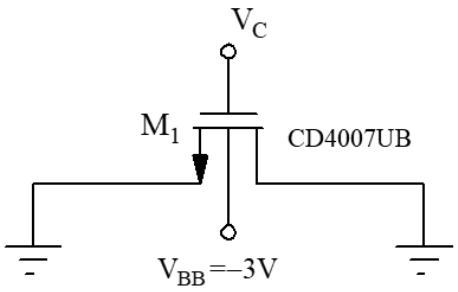


Figure PL3.1(a)

2. Gain-Controllable Amplifier

(b) For the inverting amplifier circuit shown in Fig. PL3.1(b) (which uses an op amp defined by 'lm741.mod' and an MOS transistor with parameters as in the beginning of this pre-lab defined by 'cd4007ub.mod'), calculate and tabulate (using the *Results Sheet for Preliminary Exercises*) the gain V_o/V_i of this amplifier for values of control voltage V_C ranging from 0V to 10V, in steps of 1V. Then, plot the gain versus V_C on a graph. [Hint: Be careful when determining gain at V_C=0V.]

Assume for this pre-lab that the MOS transistors have zero leakage currents. You can use results from the previous pre-lab for the op-amp characteristics.

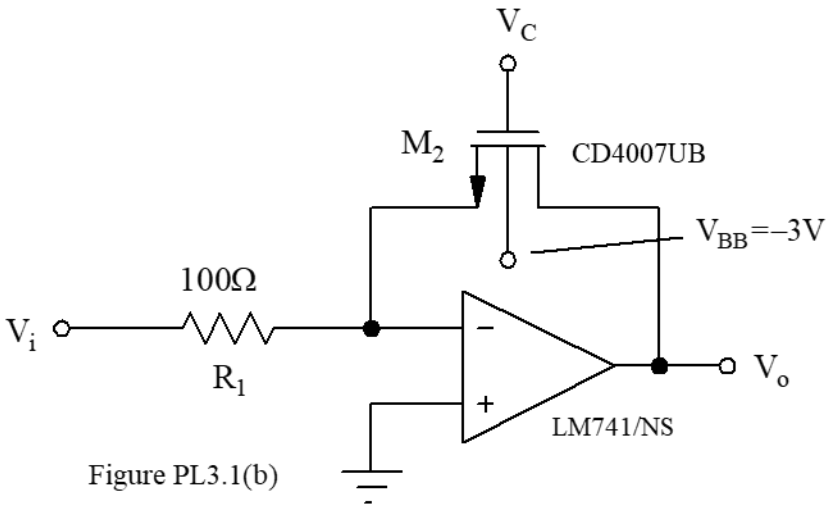


Figure PL3.1(b)

(c) Hand-calculate and tabulate (using the *Results Sheet for Preliminary Exercises*) the 3dB bandwidth of the amplifier for values of V_C ranging from 4V to 10V, in steps of 1V. Use SPICE to generate Bode plots for this amplifier, for values of V_C ranging from 1V to 10V. (Plot all curves on the same graph.) What might explain the differences in bandwidth between the hand-calculation and the simulation?

Helpful Hints for SPICE Simulation

Some notes on creating a MOSFET instance for this lab:

(1) For the NMOS transistor, you should use the model file on the course website, 'cd4007.mod'.

(2) To use an NMOS transistor in your netlist, you must first include the model file using a .include statement:

```
.include <path_to_model_file>
```

(3) Then, to create an instance of the MOSFET use the following code:

```
M<name> <drain> <gate> <source> <model_name>
```

Replace `<name>` with the desired name of your NMOS instance and `<model_name>` with the name of the NMOS model, which is defined within 'cd4007ub.mod'.

(4) To run a nested DC sweep (i.e., to sweep two sources in the same simulation), the syntax is very similar to the standard DC sweep:

```
.dc <source1> <start1> <stop1> <step1> <source2> <start2> <stop2> <step2>
```

Note that in this analysis, `<source1>` is swept and `<source2>` is stepped.

(5) To run a nested AC sweep (i.e., to do an AC sweep and step a DC source in the same simulation), the syntax is as following:

```
.ac dec <step1> <start1> <stop1> sweep <source2> <start2> <stop2> <step2>
```

Laboratory 3: Configurable Amplifiers Using Small-Signal MOS Resistors
Results Sheet for Preliminary Exercises

1. MOS transistor small-signal resistance and Gain-Controllable Amplifier

V_c (V)	(1a) R_{mos}	(2a) Gain V_o/V_i	(2b) 3dB bandwidth
0			
1			
2			
3			
4			
5			
6			
7			
8			
9			
10			

Attach the necessary annotated plots for parts (1a), (2a), and (2b).

c) Explain discrepancies between calculated bandwidth and SPICE simulation:

Laboratory 3: Configurable Amplifiers Using Small-Signal MOS Resistors Laboratory Exercises

INTRODUCTION

Objectives

This lab attempts to illustrate the small-signal operation of a nonlinear device by demonstrating a gain-controllable inverting amplifier and bandwidth-controllable lowpass filter using a small-signal MOS resistor.

Summary of Procedures

(i) Using the HP 4145/4155A/B/C, take sufficient data to determine the parameters needed to predict the small-signal resistance of two discrete MOS transistors under various gate bias voltages.

(ii) Build a gain-controllable inverting amplifier using an op amp, a resistor, and one of the discrete MOS transistors measured in (i).

(iii) Measure the gain and bandwidth of the gain-controllable amplifier under various MOS resistor gate bias voltages.

Materials Required

- HP 4145/4155A/B/C Semiconductor Parameter Analyzer
- Breadboard
- Power Supplies
- DMM
- Assorted Resistors
- CD4007UB Transistor DIP

PROCEDURE

1. Characterizing MOS Transistors

[*Note*: *This part need not be done first. If an HP 4155B is not available initially, e.g., due to some of them being down or inoperable, you can do the other parts in the lab first, then characterize the NMOS transistors you used as the last step*.]

In this part of the lab, you will again use the HP 4155B Semiconductor Parameter Analyzer, this time to measure the *IV*-characteristics of two NMOS transistors contained within the CD4007UB DIP packages. For your reference, the data sheet (including the pin-out) for the CD4007UB transistor DIP is online. Note that this chip contains both NMOS and PMOS

transistors, as well as an inverter circuit. Be careful to choose one *NMOS* transistor, not PMOS, for this part.

(a) You will need to configure the HP 4155A/B/C for MOS I_D versus V_{DS}/V_{GS} curve measurement. You will set up the sweeps using the same procedures as in Lab 2, though this time you will configure the HP 4155B to test an NMOS device hooked up through the HP16058 Test Fixture as summarized in Table L3.1(a). The procedure is similar for the HP 4145 but the front panel layout is different.

TABLE L3.1(a). HP 4155B Connections for MOS Device Curve Measurement

HP 4155B Connector	Represented Voltage	Connect To:
SMU1	V_S	source
SMU2	V_{DS}	drain
SMU3	V_{GS}	gate
SMU4	V_B	bulk

Using the hookup indicated in Table L3.1(a), use the following procedure to measure the I_D versus V_{DS}/V_{GS} curves (for V_{DS} ranging from 0V to 5V, and V_{GS} ranging from 0V to 10V, in steps of 1V, with V_B= –3V) and obtain a data plot for one of the NMOS transistors in your CD4007UB chip. Some screenshots of the 4145 and 4155 panels are provided at the end of this manual.

[The HP 4155A/B/C has two types of keys: "hard" keys, which are dedicated buttons on the front panel, and a column of "soft" keys, just to the right of the screen. In the procedure below, a KEY is a hard key, and a KEY is a soft key.]

(1) CHAN to navigate to the "CHANNEL DEFINITION" screen. Name the channels according to Table L3.1(a) above. Be sure to set V_{DS} to VAR1 and V_{GS} to VAR2, which will allow you to sweep V_{DS} while stepping V_{GS}.

(2) MEAS to get to the "SWEEP SETUP" screen. Set the sweep parameters so that V_{DS} is swept from 0V to 5V (in steps of at most 100mV) and V_{GS} is swept from 0V to 10V in 1V steps. Be sure to ground V_S and set V_B to -3V.

(3) DISPLAY to get to the "DISPLAY SETUP" screen. Here you should set the axes according to the type of characteristic you want to plot. For example, $I_d - V_{DS}$ curves would be plotted with V_{DS} on the x-axis and I_D on the y-axis. Note that for the $I_D - V_{GS}$ curves, you should set V_{DS} to be a CONST voltage while sweeping V_{GS}.

(4) GRAPH/LIST to get the "GRAPHICS PLOT" window.

(5) SINGLE to perform the measurement.

(6) SCALING, AUTOSCALING if necessary to view the whole plot.

Now, measure the slope in the linear region of the V_{GS}=5V curve using a measurement line as follows:

(7) MARKER/ CURSOR | MARKER OFF to turn marker on (the soft key will now read MARKER ON); move it to first point with the knob.

(8) MARKER SKIP to move from curve to curve in the characteristic until you reach the V_{GS}=5V curve.

(9) CURSOR OFF to turn on the short cursor. The soft key will now read CURSOR SHORT.

(10) LINE, CURSOR TO MARKER to move the currently selected cursor to the current marker position.

(11) LINE, LINE SELECT NONE to turn line options on (the soft key should read LINE SELECT 1).

(12) SELECT CURSOR 1 to switch the currently selected cursor to CURSOR 2. The soft key should now read SELECT CURSOR 2.

(13) Move the marker to the second point with the knob, then press CURSOR TO MARKER to move the selected cursor (2) to the new marker position.

(14) LINE OFF to turn on the line, which should be drawn between the two cursors you have positioned. The soft key should now read LINE ON.

(15) You can then now read the intercept and gradient values for the drawn line from the display. Be sure that grad mode is off.

From the slope just determined, calculate the value of r_{ds} in the linear region for this transistor with V_{GS}=5V.

(b) With the same transistor-to-test fixture hookup as in (a), measure the I_D versus V_{GS} characteristic for values of V_B ranging from 0 to –5V in 1V increments (with V_{DS} = 50mV), plot it, and determine the zero-bulk-bias threshold voltage for your NMOS device using the following procedure:

(1) GRAPH/LIST to get the "GRAPHICS PLOT" window.

(2) SINGLE to perform the measurement.

(3) SCALING, AUTOSCALING if necessary to view the whole plot.

Now, determine the threshold voltage by locating the apparent point where the curve intersects the V_{GS}-axis (c.f., Fig. **Error! Reference source not found.**). Do this using the measurement line as described in part (a), being sure to place the measurement line along the steep part of the curve.

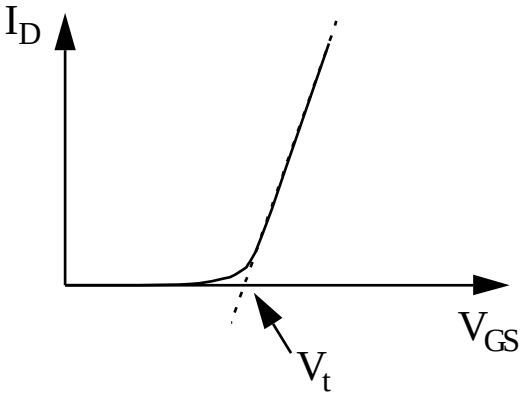


Figure L3.1 Determination of V_t from the I_D vs. V_{GS} curve for a linear MOSFET.

(c) Still with the same transistor-to-test-fixture hookups, measure the drain-to-source resistance r_{ds} (on a log scale) versus V_{GS} characteristic as follows:

(1) CHAN to navigate to the "CHANNEL DEFINITION" screen. You can create a user defined function for RDS=VD/ID.

(2) DISPLAY to get to the "DISPLAY SETUP" page. This page defines the plot(s) to be measured when you hit SINGLE. At this point, the page is setup to plot I_D (defined in the Y1-axis column) versus V_{GS} (defined in the X-axis column).

(3) Move the pointer to the Y1-axis column and select "RDS" from the soft-keys as the Y1-axis name. "RDS" is a defined function (defined on the "CHANNELS: USER

FUNCTION DEFINITION" page) that calculates the r_{ds} resistance for you from the I_D versus V_{GS} data that the HP 4155B measures. Switch to "LOG" scale for the Y1-axis and set the minimum and maximum scale values to 100 and 100000, respectively. Now, you have effectively set up the HP 4155B to measure the MOS small-signal resistance r_{ds} as a function of gate voltage $V_{GS}=V_C$.

(4) GRAPH/LIST to get the "GRAPHICS PLOT" window.

(5) SINGLE to perform the measurement.

(6) SCALING, AUTOSCALING if necessary to view the whole plot.

(d) Repeat steps (a) through (c) for another NMOS transistor on your CD4007UB chip. Keep track of which transistor is which. Call the first one M_1 and call the second one M_2.

2. Gain-Controllable Amplifier

(a) Hook up the circuit in Fig. PL3.1(b) and apply a 0.2Vpp, 10-kHz sinewave to the input of the circuit. Use your oscilloscope to measure the low frequency gain V_o/V_i and 3dB bandwidth of this amplifier for values of control voltage V_C ranging from 2V to 10V, in steps of 1V. Tabulate your data using the "measured" sections of Table LR3.2 in the *Results Sheet for Laboratory Exercises*, then plot the gain versus V_C and 3dB bandwidth versus V_C on separate graphs.

Note: you may use the HP 4155B as a voltage source for the control and body signals. In the channel definition, set both VG and VB as constant, and remove the other definitions. Now navigate to the graphics windows, and use REPEAT to apply a continuous voltage. You may use STOP to turn off the measurement and go back to the previous menus.

(b) Did you see distortion for any of the V_C values? Explain.

(c) [Note: You can do this part after the lab period, if necessary.] Extract values for K_n and V_{TN} from your part 1 measurements and use these to fill in the "calculated" portions of Table LR3.2 in the *Results Sheet for Laboratory Exercises*. Then plot the gain versus V_C and 3dB bandwidth versus V_C on the same graphs as your measured data, being sure to delineate which graph is which. Comment on any discrepancies between measured and calculated data.

(d) Next, set the amplitude of the input sinewave to 5Vpp and the frequency to 10kHz. Print out a plot of the ensuing output waveform. Does the waveform look strange? Why? Now what is the gain of the amplifier? (Determine gain based on peak signals, whether they are sinusoidal or not.)

Laboratory 3: Configurable Amplifiers Using Small-Signal MOS Resistors
Results Sheet for Laboratory Exercises

NAME: _____ **LAB SECTION:** _____

2. Characterizing MOS Transistors

(a) Attach annotated HP 4155B plot of I_D vs. V_{DS}/V_{GS} curves for both M_1 and M_2. Show all calculations on the plot.

r_{ds1}(for M_1 with V_{GS1}=5V) = _____

r_{ds2}(for M_2 with V_{GS2}=5V) = _____

(b) Attach annotated HP 4155B plot of I_D versus V_{GS}. Show all calculations on the plot.

V_{t1}(for M_1) = _____

V_{t2}(for M_2) = _____

(c) Attach annotated HP 4155B plot of r_{ds} versus V_{GS}.

2. Gain-Controllable Amplifier

(a) Fill in the columns associated with the "measured" portions of Table LR3.2.

Attach the required annotated plots.

(b) Explain any distortion seen.

(c) Fill in the columns associated with the "calculated" portions of Table LR3.2.

Plot gain versus V_C and 3dB bandwidth versus V_C on the same graphs as the measured data

Table LR3.2. Gain-Configurable Amplifier Characteristics

V_C [V]	Gain, V_o/V_i		3dB BW	
	2(a) Measured	2(b) Calculated	2(a) Measured	2(b) Calculated
2				
3				
4				
5				
6				
7				
8				
9				
10				

Are there any discrepancies between the model and the measured data?

(c) Attach an annotated plot of the output waveform.

Does the waveform look strange? Why?

Gain, V_o/V_i = _____

3. GENERAL QUESTIONS

Using the data obtained in Part 3(a) of the laboratory exercises, determine the percent mismatch in K_n and V_t between the two transistors you measured. Percent mismatch can be determined using the following formula:

$$\%\text{Mismatch} = 100 \times \frac{P_2 - P_1}{P_{avg}} = 2 \times 100 \times \frac{P_2 - P_1}{P_2 + P_1}.$$

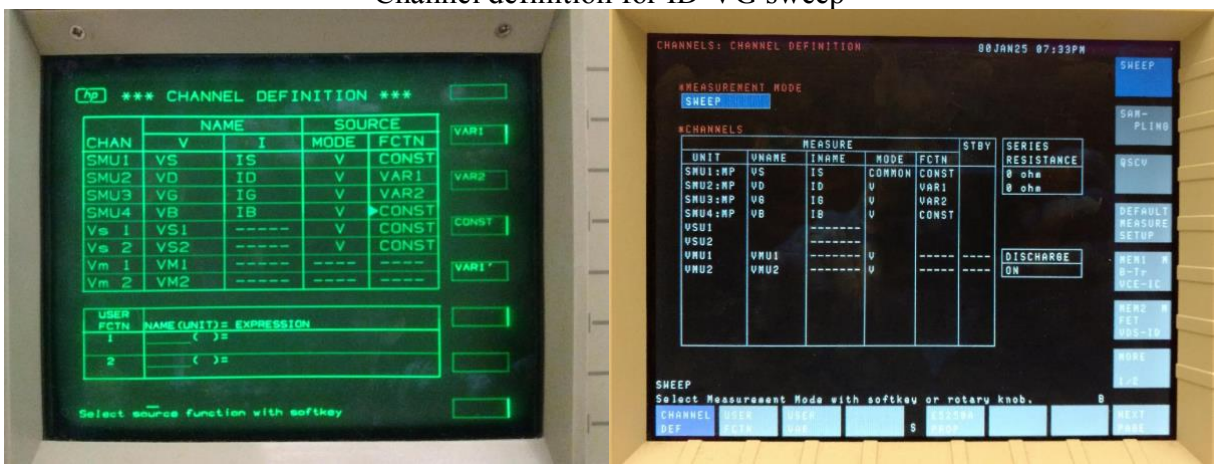
% Mismatch in K_n = _____

% Mismatch in V_t = _____

Laboratory 3: Configurable Amplifiers Using Small-Signal MOS Resistors

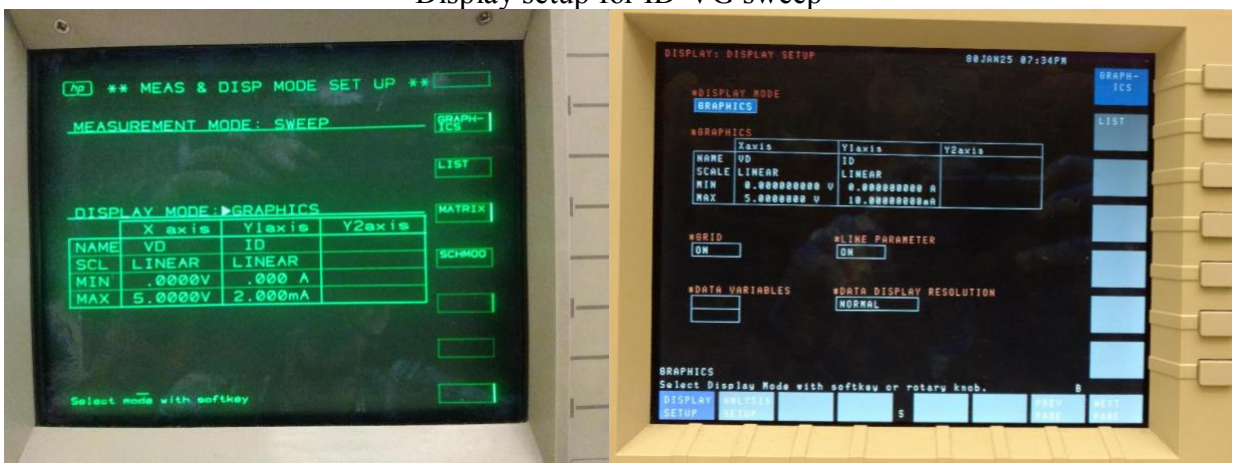
Appendix

Channel definition for ID-VG sweep



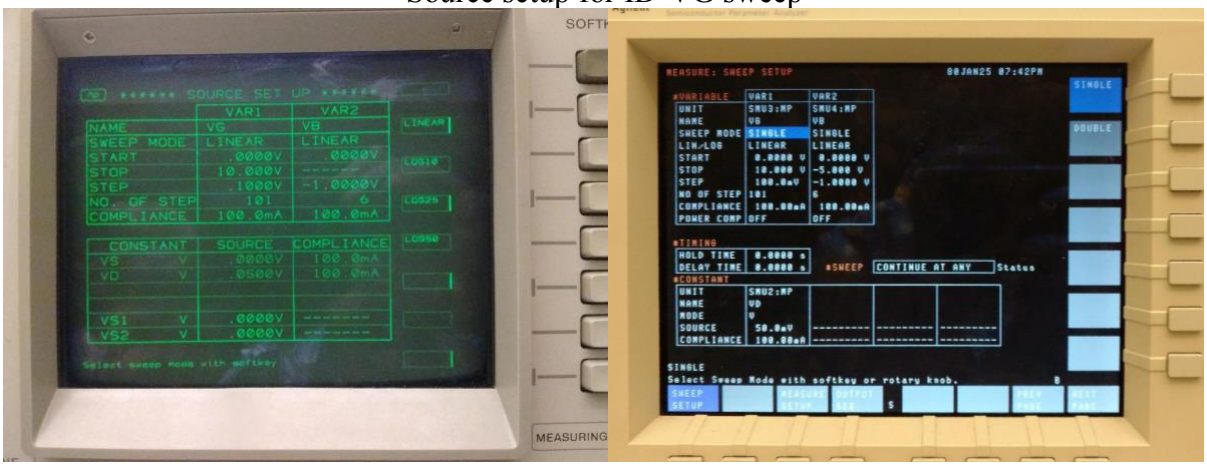
Sweep setup for ID-VG sweep

Display setup for ID-VG sweep

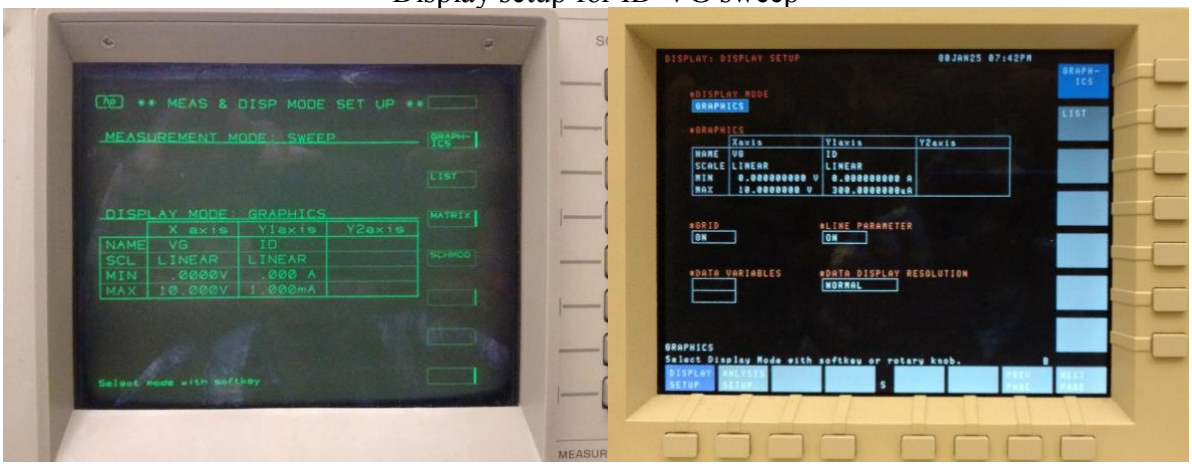


Channel definition for ID-VG sweep

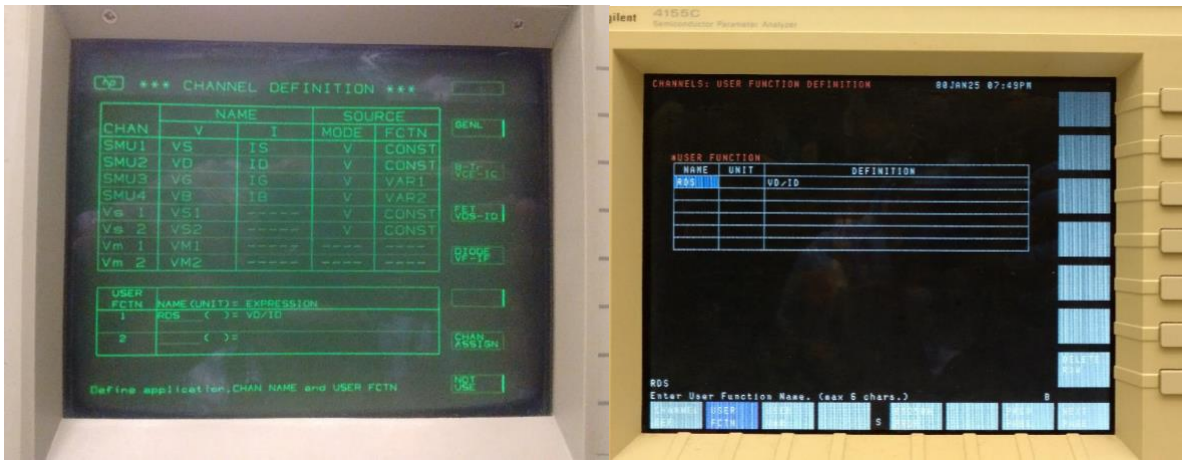
Source setup for ID-VG sweep



Display setup for ID-VG sweep



User function definition



Display setup for RDS measurement

Channel definition for constant voltage mode